

Q4

Depletion Layer Width (W_{dep})

$W_{\text{dep}} = x_p + x_n$ — (iii) [x_n and x_p are width of depletion layer on two sides of junction]
we know,

$$N_a x_p = N_d x_n$$

$$\Rightarrow x_p = (N_d / N_a) x_n \quad \text{--- (i)}$$

$$\text{or } x_n = (N_a / N_d) x_p$$

Built in potential, $\phi_{bi} = \frac{k_B T}{q} \left[\ln \frac{N_a N_d}{n_i^2} \right]$

or $\phi_{bi} = \frac{q}{2 \epsilon_s} (N_a x_p^2 + N_d x_n^2) \quad \text{--- (ii)}$

So using equation (i) and (ii)

$$x_p = \left[\frac{2 \epsilon_s \phi_{bi}}{q} \left(\frac{N_d}{N_a} \right) \left(\frac{1}{N_a + N_d} \right) \right]^{1/2} \quad \text{--- (iv)}$$

$$x_n = \left[\frac{2 \epsilon_s \phi_{bi}}{q} \left(\frac{N_a}{N_d} \right) \left(\frac{1}{N_a + N_d} \right) \right]^{1/2} \quad \text{--- (v)}$$

Using eq (ii), (iv) and (v)

$$W_{\text{dep}} = \left[\frac{2 \epsilon_s \phi_{bi}}{q} \left(\frac{N_a + N_d}{N_a N_d} \right) \right]^{1/2} = \left[\frac{2 \epsilon_s \phi_{bi}}{q} \left(\frac{1}{N_a} + \frac{1}{N_d} \right) \right]^{1/2}$$

if $N_a \gg N_d$, as in P^+N Junction

$$W_{\text{dep}} = \left[\frac{2 \epsilon_s \phi_{bi}}{q} \left(\frac{1}{N_a} + \frac{1}{N_d} \right) \right]^{1/2} \approx \left[\frac{2 \epsilon_s \phi_{bi}}{q N_d} \right]^{1/2}$$

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and

$$\chi_N = \left[\frac{2 \epsilon_s \phi_{bi}}{q} \left(\frac{N_a}{N_d} \right) \left(\frac{1}{N_a + N_d} \right) \right]^{1/2}$$

$$\approx \left[\frac{2 \epsilon_s \phi_{bi}}{q} \left(\frac{N_a}{N_d} \right) \left(\frac{1}{N_d} \right) \right]^{1/2}$$

$$\Rightarrow W_{dep} \approx \chi_N$$

$$\text{So, } \chi_p = \chi_N \frac{N_d}{N_a} \approx 0$$

\therefore for P^+N junction where $N_a \gg N_d$,

$$W_{dep} \approx \chi_N$$

$$\text{and } \chi_p \approx 0$$

Similarly for an N^+P junction where $N_d \gg N_a$,

$$W_{dep} \approx \chi_p \text{ and } \chi_N \approx 0$$

So, depletion layer width is determined by higher doping concentration.

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